

DOCKET NO: 241280US2S DIV

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

IN RE APPLICATION OF :  
TSUTOMU SATO ET AL. :  
SERIAL NO: NEW APPLICATION :ATT: APPLICATION DIVISION  
FILED: HEREWITH :  
FOR: SEMICONDUCTOR DEVICE :  
FORMED IN SEMICONDUCTOR LAYER :  
ARRANGED ON SUBSTRATE WITH :  
ONE OF INSULATING FILM AND :  
CAVITY INTERPOSED BETWEEN THE :  
SUBSTRATE AND THE :  
SEMICONDUCTOR LAYER :

PRELIMINARY AMENDMENT

COMMISSIONER FOR PATENTS  
ALEXANDRIA, VIRGINIA 22313

SIR:

Prior to examination on the merits, please amend the above-identified application as follows:

**Amendments to the Specification** begin on page 2 of this paper.

**Amendments to the Claims** are reflected in the listing of claims which begins on page 3 of this paper.

**Remarks** begin on page 6 of this paper.